

isc Thyristors

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S6008L

TO-220

DESCRIPTION

- With TO-220 isolated packaging
- Electrically-isolated package
- High surge capability
- Glass passivated junctions and center gate fire for greater parameter uniformity and stability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

· Switching applications

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

PARAMETER			MIN	UNIT				
Repetitive peak off-state voltage			600	V				
Repetitive peak reverse voltage			600	V				
RMS on-state current			8	Α				
Surge non-repetitive on-state current (1/2 cycle,sine wave;Tc=25℃)		50HZ 60HZ	83 100	Α				
Average gate power dissipation	Tp=8.3ms		0.5	W				
Operating junction temperature	9		-40~125	°C				
Storage temperature			-40~150	°C				
	PARAMETER Repetitive peak off-state voltage Repetitive peak reverse voltage RMS on-state current Surge non-repetitive on-state current (1/2 cycle,sine wave;Tc=25°C) Average gate power dissipation Operating junction temperature	PARAMETER Repetitive peak off-state voltage Repetitive peak reverse voltage RMS on-state current Surge non-repetitive on-state current (1/2 cycle,sine wave;Tc=25°C) Average gate power dissipation Tp=8.3ms Operating junction temperature	PARAMETER Repetitive peak off-state voltage Repetitive peak reverse voltage RMS on-state current Surge non-repetitive on-state current (1/2 cycle,sine wave;Tc=25°C) Average gate power dissipation Tp=8.3ms Operating junction temperature	PARAMETERMINRepetitive peak off-state voltage600Repetitive peak reverse voltage600RMS on-state current8Surge non-repetitive on-state current50HZ(1/2 cycle,sine wave;Tc=25°C)50HZAverage gate power dissipationTp=8.3ms0.50perating junction temperature				

ELECTRICAL CHARACTERISTICS (Tc=25[°]C unless otherwise specified)

SYMBOL	PARAMETER	CONDITIONS		MIN	МАХ	UNIT
I _{RRM}	Repetitive peak reverse current	V _{RM} =V _{RRM}	Tj=25℃		0.01	
I _{DRM}	Repetitive peak off-state current	V _{DM} =V _{DRM}	Tj=100℃ Tj=125℃		0.2 0.5	mA
V _{TM}	On-state voltage	I _{TM} = 8A			1.6	V
I _{GT}	Gate-trigger current	V _D = 12 V; RL=60 Ω			15	mA
V _{GT}	Gate-trigger voltage	V _D = 12 V; RL=60 Ω			1.5	V
R _{th(j-c)}	Thermal resistance	Junction to case			3.0	°C/W

isc website: <u>www.iscsemi.com</u>

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